# FSUSB242 Type-C USB Port Protection Switch

#### **Features**

- Fully USB Data Port Protection
- V<sub>DD</sub> 0 V 5.5 V (12 V DC tolerant)
- -18 V to +20 V DC Tolerance on HSD± Port
- ±25 V IEC 61000-4-5 Surge Protection w/o External TVS
- V<sub>DD</sub> Operating Range, 2.7 V–5.5 V
- HSD RON: 5 Ω Typical
- C<sub>ON</sub> = 5 pF Typical
- Wide -3 dB Bandwidth: > 720 MHz
- Low Power Operation:  $I_{CC} < 10 \mu A$  (Typical)
- Over Voltage Protection: 3.6 V & 4.5 V

#### **Typical Applications**

- Smartphones
- Tablets
- Laptops

#### Safety Mechanisms Highlight

- 3.6 V & 4.5 V OVP Trip Point
- ±25 V Surge Protection without Need for External TVS

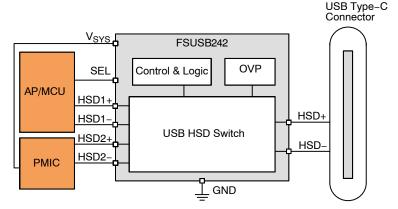


Figure 1. Application Schematic



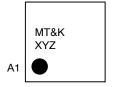
### ON Semiconductor®

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WLCSP9 1.20 × 1.20 CASE 567UL

#### **MARKING DIAGRAM**

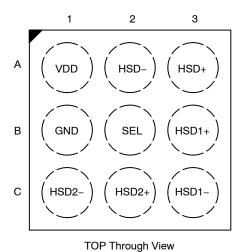


MT = Specific Device Code&K = 2 Digit Lot Run Code

X = Year

Y = 2 Week Data Code Z = Plant Code

#### **PIN CONNECTION**



ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

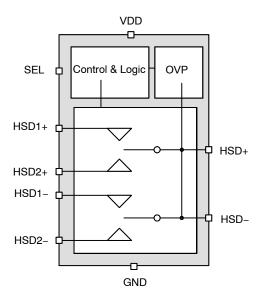


Figure 2. Simplified Block Diagram

**Table 1. PIN FUNCTION DESCRIPTION** 

CSP Bump	Name	Туре	Description
A1	VDD	Power	Supply Power
B1	GND	Ground	Ground
A3	HSD+	Data	Common High Speed Data Bus
A2	HSD-	Data	Common High Speed Data Bus
B3	HSD1+	Data	Multiplexed High Speed Data Port 1
СЗ	HSD1-	Data	Multiplexed High Speed Data Port 1
C2	HSD2+	Data	Multiplexed High Speed Data Port 2
C1	HSD2-	Data	Multiplexed High Speed Data Port 2
B2	SEL	I/O	Tri-Input HSD Switch Select & /OE

**Table 2. SWITCH TRUTH TABLE CONFIGURATION** 

VDD	SEL	Switch Configuration
UVLO	X	Switch off High impedance
Valid	0	HSD+ = HSD1+, HSD- = HSD1-
Valid	1	HSD+ = HSD2+, HSD- = HSD2-
Valid	Float/High-Z	Switch Disable High impedance

#### **APPLICATION INFORMATION**

#### **Over Voltage Protection**

Over voltage protection turns the switch off if the inputs HSD+/HSD- rise above the over voltage trip threshold.

### **Under Voltage Lockout**

The under-voltage lockout on  $V_{DD}$  pin turns the switch off if the  $V_{DD}$  voltage drops below the lockout threshold. With the SELpin active, the input voltage rising above the UVLO threshold releases the lockout and enables the switch.

#### Tri-State Input Control Pin (SEL)

The SEL pin can be tri-stated to disable the switch to save power, there are a few ways to achieve this. If the SEL pin is controlled by GPIO in the system, if the GPIO pin has a High-Z state where the impedance of the High-Z state is

larger then 2 M $\Omega$  the switch will recognize the High–Z state and disable the switch. If the system does not have GPIO that supports High–Z state, the user can utilize 2 MOSFETs or a Logic Device to achieve the same result.

#### For GPIO

The SEL pin function below:

- If the input is pulled up with less than 50 k $\Omega$  it will be considered as Logic High
- If the input is pulled down with less than 50 k $\Omega$  it will be consider as Logic Low
- If the input is pulled up or down with more 4 M $\Omega$  it will be consider as float/High–Z

#### **System Timing Diagram**

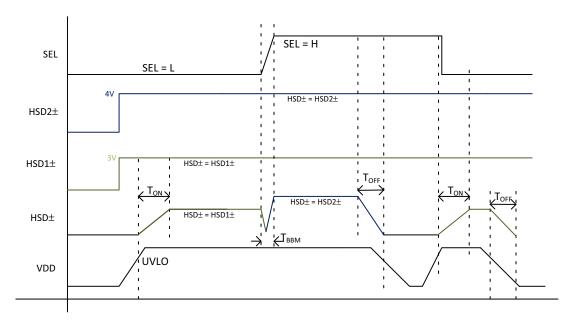


Figure 3. System Timing Plot

#### **System Block Diagrams**

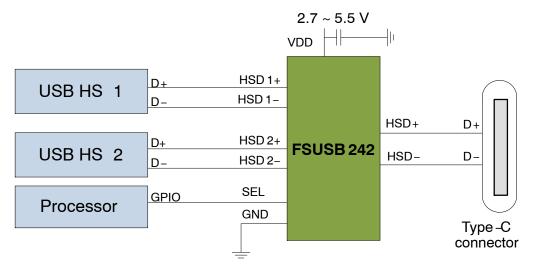


Figure 4. Application of 2x USB HS interface

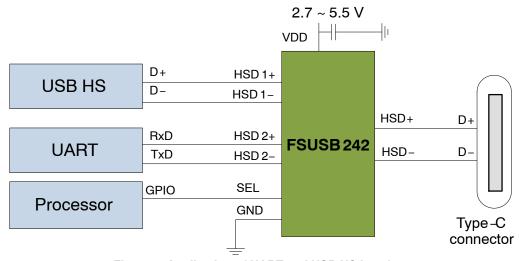


Figure 5. Application of UART and USB HS interface

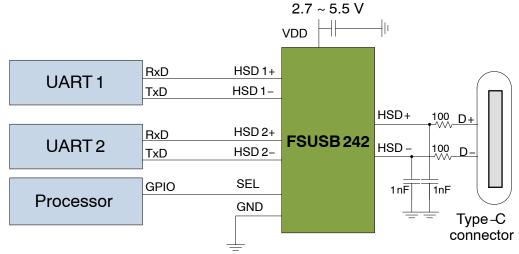


Figure 6. Application of 2x UART interface

When 2x UART signals are switched over FSUSB242, both 100 ohm series resistor and 1 nF bypass capacitors are recommended in the common switch path as above. If FSUSB242 is used to switch USB and UART signals, connect UART signals to HSD1.

# **USB High Speed Eye Diagram**

# $V_{DD} = 5.5 \ V \ HSD \ to \ HSD1 \ Path$

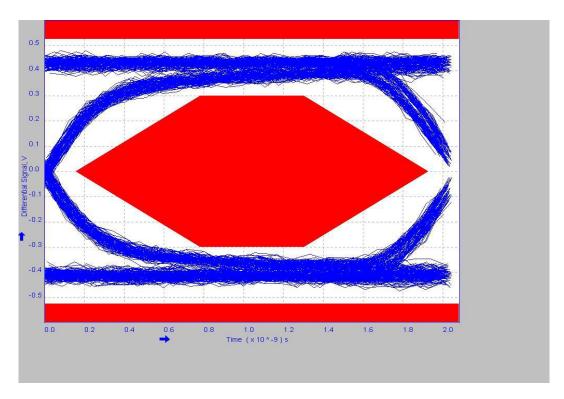


Figure 7. HS USB Eye @  $V_{DD}$  = 5 V

 $V_{DD} = 2.7 \ V \ HSD \ to \ HSD2 \ Path$ 

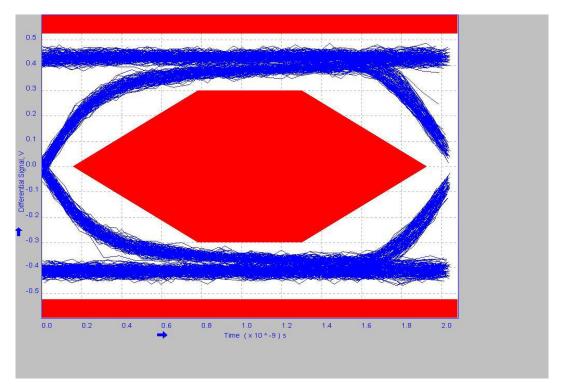


Figure 8. HS USB Eye @  $V_{DD}$  = 2.7 V

**Table 3. ABSOLUTE MAXIMUM RATINGS** 

Symbol	Parameter				Max	Unit
V <sub>DD</sub>	Supply Voltage from V <sub>DD</sub>				12.0	V
V <sub>SW</sub>	DC Input voltage tolerance for HSD±, to	GND		-18	20	V
	DC Input voltage tolerance for HSD1±, I	HSD2± to GND		-1.2	6	V
V <sub>CONTROL</sub>	DC Input Voltage (SEL)			-0.5	6	V
I <sub>SW</sub>	DC HSD Switch Current				100	mA
I <sub>IK</sub>	DC Input Diode Current			-50		mA
T <sub>STORAGE</sub>	Storage Temperature Range			-65	+150	°C
TJ	Maximum Junction Temperature				+150	°C
TL	Lead Temperature (Soldering, 10 secon	ids)			+260	°C
ESD	IEC 61000-4-2 System ESD (Note 1)	Connector Pins (HSD±)	Air Gap	15		kV
			Contact	8		
	Human Body Model, JEDEC	Power to GND	•	2		kV
	JESD22-A114	Internal Pin to GND (HSE	)1±, HSD2±)	2		
		External Pin to GND (HSD±)		14		
	Charged Device Model, JEDEC LESD22-C101	All Pins		1		
	IEC 61000-4-5 Surge Protection	HSD±, to GND		±25		V
		V <sub>DD</sub> to GND		+12		V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**Table 4. RECOMMENDED OPERATING CONDITIONS** 

Symbol	Parameter	Min	Тур	Max	Unit
V <sub>DD</sub>	Supply Voltage	2.7	4.2	5.5	V
V <sub>SW1</sub>	HSD1 Switch I/O Signal Swing Voltage (Note 2)	-0.5		3.6	V
V <sub>SW2</sub>	HSD2 Switch I/O Signal Swing Voltage (Note 2)	-0.5		4.5	V
I <sub>CCSW</sub>	Maximum HSD Switch Continuous Current			75	mA
V <sub>CNTRL</sub>	Control Input Voltage (SEL)	-0.5		$V_{DD}$	V
T <sub>A</sub>	Operating Temperature	-40		+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

#### **Table 5. DC ELECTRICAL CHARACTERISTICS**

(Unless otherwise specified: Recommended  $T_A$  and  $T_J$  temperature ranges. All typical values are at  $T_A$  = 25°C and  $V_{DD}$  = 4.2 V unless otherwise specified.)

				T <sub>A</sub> = -40 to +85°C T <sub>J</sub> = -40 to +125°C			
Symbol	Characteristic	V <sub>DD</sub> (V)	Conditions	Min	Тур	Max	Unit
BASIC OPE	BASIC OPERATION DEVICE						
I <sub>CC</sub>	Quiescent Supply Current	2.7 to 5.5	WLCSP: /OE = H & L, I <sub>OUT</sub> = 0		10		μΑ
I <sub>OFF</sub>	Power-Off Leakage Current	0	V <sub>SWHSD1</sub> = 0 V to 3.6 V, V <sub>SWHSD2</sub> = 0 V to 4.5 V	-3		3	μΑ

<sup>1.</sup> System level test that depends on end system for actual performance. These tests results are with external TVS protection. These specs are listed as general guidelines for expected performance in actual system and do not guarantee listed performance.

<sup>2.</sup> The switch swing voltage is based on the OVP trip level, and when OVP triggers the switch will be disabled to protect the host and no longer in the standard operating condition, once over voltage is removed the device will automatically recover back to normal condition.

# Table 5. DC ELECTRICAL CHARACTERISTICS (continued)

(Unless otherwise specified: Recommended  $T_A$  and  $T_J$  temperature ranges. All typical values are at  $T_A = 25^{\circ}C$  and  $V_{DD} = 4.2 \text{ V}$  unless otherwise specified.)

				T <sub>A</sub> = -40 to +85°C T <sub>J</sub> = -40 to +125°C			
Symbol Characteristic		V <sub>DD</sub> (V) Conditions		Min	Тур	Max	Unit
BASIC OPI	ERATION DEVICE						
I <sub>IN</sub>	Control Input Leakage	2.7 to 5.5	V <sub>CNTRL</sub> = 0 V to V <sub>DD</sub>	-2		4	μΑ
I <sub>OZ</sub>	Off State Leakage	2.7 to 5.5	HSD± ≥ 0 V, HSD1±, HSD2± ≤ 3.6 V	-3		5	μΑ
BASIC OPI	ERATION HSD SWITCH	•			1	•	
R <sub>ON</sub>	HSD Path On Resistance	2.7 to 5.5	I <sub>OUT</sub> = 8 mA, V <sub>SW</sub> = 0 V to 0.4 V		5		Ω
$\Delta R_{ON}$	HSD Path Delta R <sub>ON</sub>	2.7 to 5.5	I <sub>OUT</sub> = 8 mA, V <sub>SW</sub> = 0 V to 0.4 V		0.15		Ω
V <sub>IH</sub>	SEL Input Voltage High	2.7 to 5.5		1.3			V
$V_{\text{IM}}$	SEL Input Voltage Middle (Note 3)	2.7 to 5.5		0.8		1.0	٧
$V_{IL}$	SEL Input Voltage Low	2.7 to 5.5				0.5	٧
Zfloat	Impedance to VDD or GND detected as a Float including $V_{DD} = 0$	2.7 to 5.5		2.5			МΩ
V <sub>OV_TRIP1</sub>	Input OVP Lockout for HSD1	2.7 to 5.5	V <sub>HSD±</sub> Rising, SEL = 0	3.6	3.8	4	V
			V <sub>HSD±</sub> Falling, SEL = 0	3.3	3.5		
V <sub>OV_TRIP2</sub>	Input OVP Lockout for HSD2	2.7 to 5.5	V <sub>HSD±</sub> Rising, SEL = 1	4.5	4.7	4.9	٧
			V <sub>HSD±</sub> Falling, SEL = 1	4.2	4.4		
V <sub>OV_HYS</sub>	Input OVP Hysteresis	2.7 to 5.5			0.3		٧
V <sub>NV_TRIP</sub>	Input Negative Voltage Lockout	2.7 to 5.5	V <sub>HSD±</sub> Falling		-1.0		٧
			V <sub>HSD±</sub> Rising		-0.7		
V <sub>NV_HYS</sub>	Input OVP Hysteresis	2.7 to 5.5			0.3		٧
$V_{CL}$	Clamping Voltage	2.7 to 5.5	V <sub>HSD±</sub> ≥ V <sub>OV_TRIP</sub>		4.5		٧
V <sub>UVLO</sub>	Under-Voltage Lockout		V <sub>DD</sub> Rising		2.4	2.7	V
			V <sub>DD</sub> Falling		2.3		
TSD	Thermal Shutdown (Note 3)		Shutdown Threshold		150		°C
			Return from Shutdown		130		
			Hysteresis		20		]

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Guaranteed by characterization or Design, not production tested.

# Table 6. AC ELECTRICAL CHARACTERISTICS

(Unless otherwise specified: Recommended  $T_A$  and  $T_J$  temperature ranges. All typical values are at  $T_A$  = 25°C and  $V_{DD}$  = 4.2 V unless otherwise specified.)

	Characteristic	V <sub>DD</sub> (V) Conditions	$T_A = -40 \text{ to } +85^{\circ}\text{C}$ $T_J = -40 \text{ to } +125^{\circ}\text{C}$				
Symbol			Conditions	Min	Тур	Max	Unit
HSD SWIT	CH TIMING PARAMETER						
t <sub>OVP</sub>	OVP Response Time (Note 43)	2.7 to 5.5	$I_{OUT}$ = 8 mA, $C_L$ = 5 pF, $R_L$ = 50 $\Omega$ , $V_{HSD\pm}$ = 3.3 V to 4.9 V		0.35		μs
t <sub>ON</sub>	Turn-On Time, SEL to Output	2.7 to 5.5	$R_L$ = 50 $\Omega$ , $C_L$ = 5 pF		0.1		ms
t <sub>OFF</sub>	Turn-Off Time, SEL to Output	2.7 to 5.5	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $V_{SW} = 0.8 V$		0.2		μs
t <sub>PD</sub>	Propagation Delay (Note 4)	2.7 to 5.5	$\begin{aligned} R_L &= 50 \ \Omega, \ C_L = 5 \ pF, \\ V_{SW} &= 0.8 \ V \end{aligned}$		1.3		ns
t <sub>BBM</sub>	Break-Before-Make (Note 4)	2.7 to 5.5	$R_L = 50 \Omega, C_L = 5 pF,$ $V_{SW1} = V_{SW2} = 0.8 V$		50		μs
t <sub>SK(P)</sub>	Skew of Opposite Transitions of the Same Output (Note 4)	2.7 to 5.5	$V_{SW}$ = 0.2 Vdiff <sub>PP</sub> , $R_L$ = 50 $\Omega$ , $C_L$ = 5 pF		35		ps
tı	Total Jitter (Note 4)	2.7 to 5.5	$V_{SW} = 0.2 \text{ Vdiff}_{PP}, R_L = 50 \ \Omega,$ $C_L = 5 \text{ pF}, t_R = t_F = 500 \text{ ps}$ $(10-90\%) \ @ 480 \text{ Mbps}$ $(PRBS = 2^{15} - 1)$		250		ps
HSD± SWI	TCH CAPACITANCE			•	•	•	•
C <sub>IN</sub>	Control Pin Input Capacitance (Note 4)	0			1.5		pF
C <sub>ON</sub>	HSD± On Capacitance (Note 4)	2.7 to 5.5	SEL = L/H, f = 240 MHz		4		
C <sub>OFF</sub>	HSD± Off Capacitance (Note 4)	2.7 to 5.5	SEL = Float, f = 240 MHz		3		
HSD SWIT	CH BANDWIDTH						
BW	-3dB SDD21 Bandwidth	2.7 to 5.5	$R_L = 50 \Omega$ , $C_L = 0 pF$		1000		MHz
	(Note 4)		R <sub>L</sub> = 50 Ω, C <sub>L</sub> = 5 pF		550		MHz
HSD SWIT	CH AC PARAMETER						
O <sub>IRR</sub>	Off Isolation (Note 4)	2.7 to 5.5	R <sub>L</sub> = 50 Ω, f = 240 MHz		-35		dB
Xtalk	Non-Adjacent Channel Crosstalk (Note 4)	2.7 to 5.5	$R_L$ = 50 $\Omega$ , f = 240 MHz		-40		dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Guaranteed by characterization or Design, not production tested.

#### **TEST DIAGRAMS**

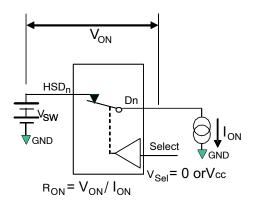
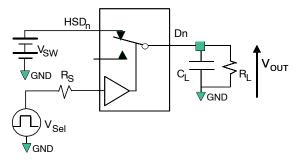


Figure 9. On Resistance



 $R_L$ ,  $R_S$ , and  $C_L$  are functions of the application environment (see AC Tables for specific values)  $C_L$  includes test fixture and stray capacitance.

Figure 11. AC Test Circuit Load

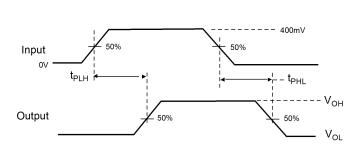
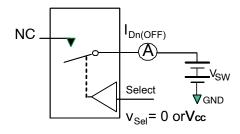


Figure 13. Propagation Delay (t<sub>R</sub>t<sub>F</sub> - 500 ps)



\*\*Each switch port is tested separately

Figure 10. Off Leakage

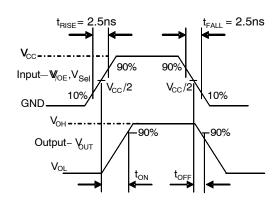


Figure 12. Turn-On / Turn-Off Waveforms

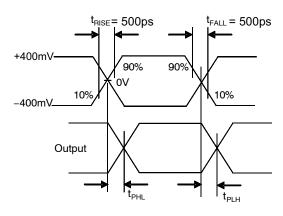


Figure 14. Intra-Pair Skew Test t<sub>SK(P)</sub>

### **TEST DIAGRAMS** (Continued)

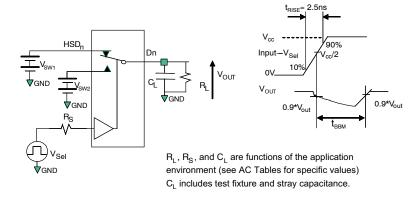


Figure 15. Break-Before-Make Interval Timing

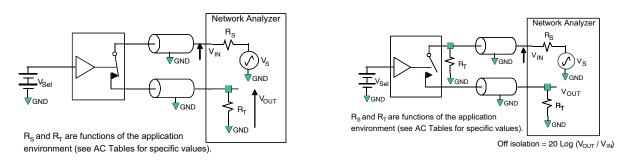


Figure 16. Bandwidth

Figure 17. Channel Off Isolation

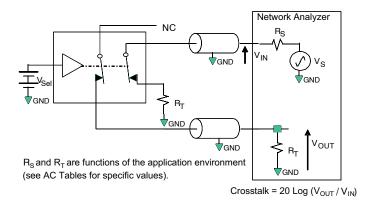
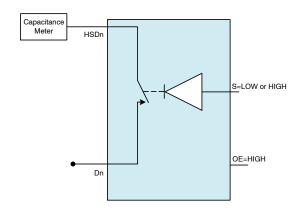


Figure 18. Non-Adjacent Channel-to-Channel Crosstalk

# TEST DIAGRAMS (Continued)



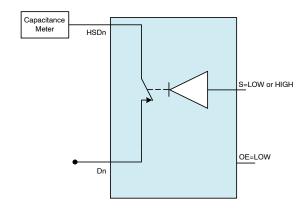


Figure 19. Channel Off Capacitance

Figure 20. Channel On Capacitance

# **ORDERING INFORMATION**

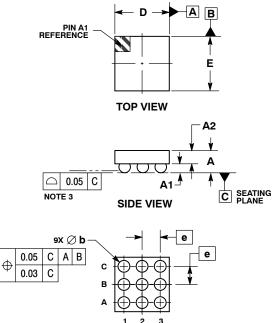
**Table 7. AVAILABLE PART NUMBERS** 

Part Number	Device Code	Operating Temperature Range	Package	Packing Method†
FSUSB242UCX	MT	−40 to 85°C	9-Ball WLCSP (1.20 x 1.20 mm)	Tape and Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

#### WLCSP9, 1.2x1.2x0.48 CASE 567UL **ISSUE A**

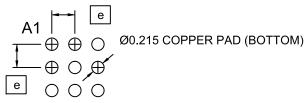


**BOTTOM VIEW** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 2009. CONTROLLING DIMENSION: MILLIMETERS. COPLANARITY APPLIES TO THE SPHERICAL CROWNS OF THE SOLDER BALLS.

	MILLIMETERS						
DIM	MIN NOM MAX						
Α	0.450	0.488	0.526				
A1	0.176	0.196	0.216				
A2	0.274	0.292	0.310				
b	0.24	0.26	0.28				
D	1.14	1.20	1.26				
Е	1.14	1.20	1.26				
е	0.40 BSC						

# RECOMMENDED SOLDERING FOOTPRINT\* (NSMD PAD TYPE)



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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